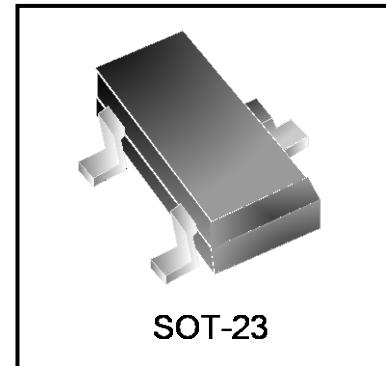



WM05N02M
N-Channel MOSFET

Features

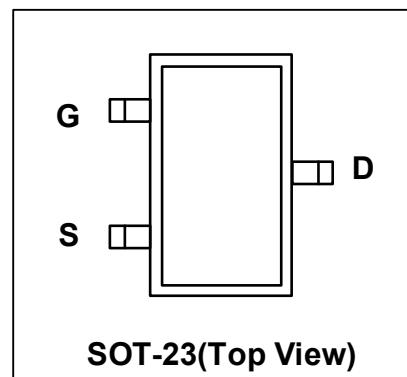
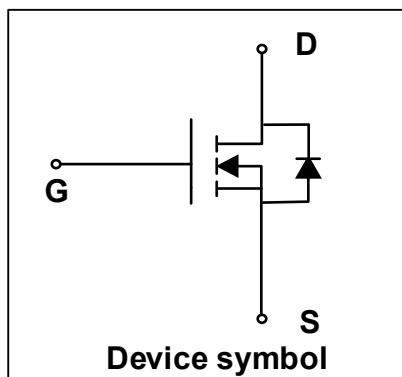
- $V_{DS} = 50V$, $I_D = 0.2A$
- $R_{DS(on)} < 3.5\Omega$ @ $V_{GS} = 10V$
- $R_{DS(on)} < 6\Omega$ @ $V_{GS} = 4.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/output Leakage



Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	V
Continuous Drain Current	I_D	0.2	A
Pulsed Drain Current ²	I_{DM}	1	A
Gate-Source Voltage Continuous	V_{GS}	± 20	V
Power Dissipation	P_D	300	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 to +150	°C
Thermal Resistance from Junction to Ambient ¹	$R_{\theta JA}$	417	°C/W

Electrical Characteristics (T_{amb}=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} = 0 V, I _D = 250μA	50	-	-	V
Drain Cut-off Current	I _{DSS}	V _{DS} = 50V, V _{GS} = 0 V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20V	-	-	±100	nA
Drain-Source on-State Resistance ³	R_{DS(on)}	V _{GS} = 10V, I _D = 0.2A	-	1.1	3.5	Ω
		V _{GS} = 4.5V, I _D = 0.2A	-	1.2	6	
Gate Threshold Voltage ³	V_{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.5	-	1.5	V
Dynamic Characteristics						
Input Capacitance	C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	31	-	pF
Output Capacitance	C_{oss}		-	4.9	-	
Reverse Transfer Capacitance	C_{rss}		-	2.5	-	
Switching Characteristics						
Turn-on Delay Time ⁴	t_{d(on)}	V _{DD} = 30V, I _D = 0.2A, R _G = 6Ω	-	5	-	nS
Rise Time ⁴	t_r		-	18	-	
Turn-off Delay Time ⁴	t_{d(off)}		-	36	-	
Fall Time ⁴	t_f		-	14	-	
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	I _S = 0.2A, V _{GS} = 0V	-	-	1.4	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch..
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing

Typical Characteristics

Figure 1. Output Characteristics

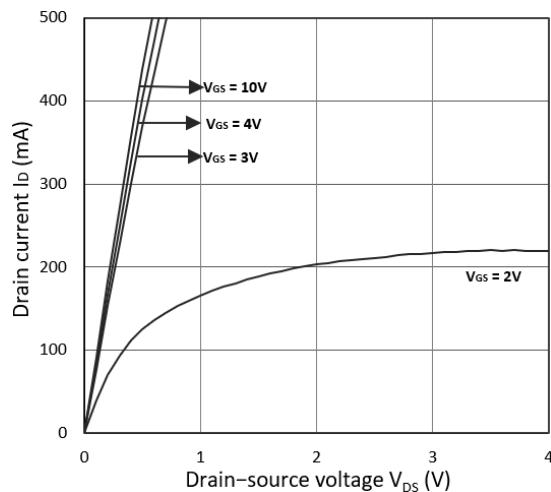


Figure 2. Transfer Characteristics

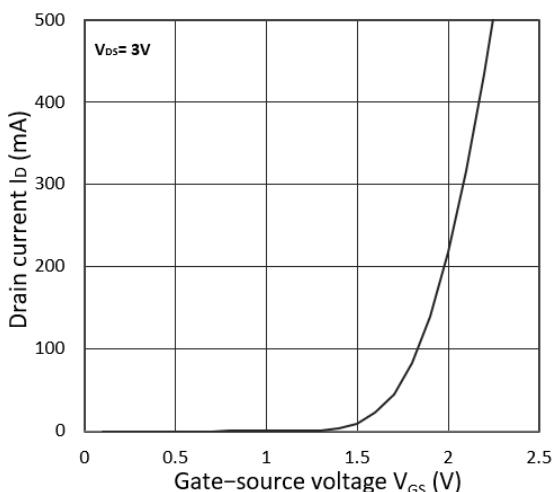
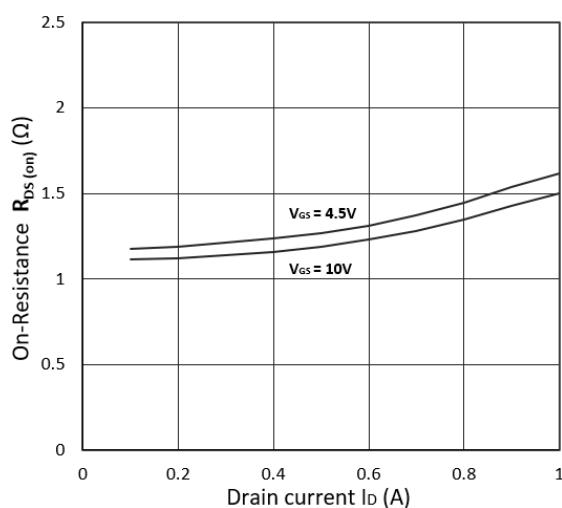
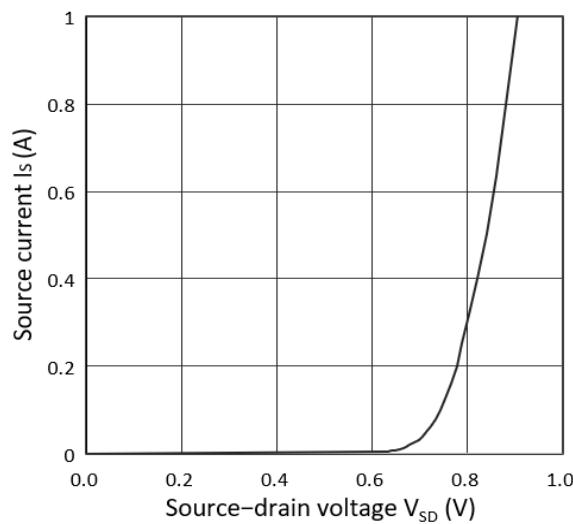
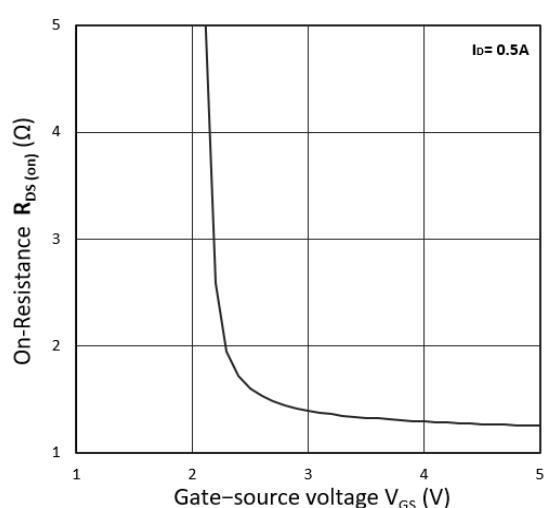
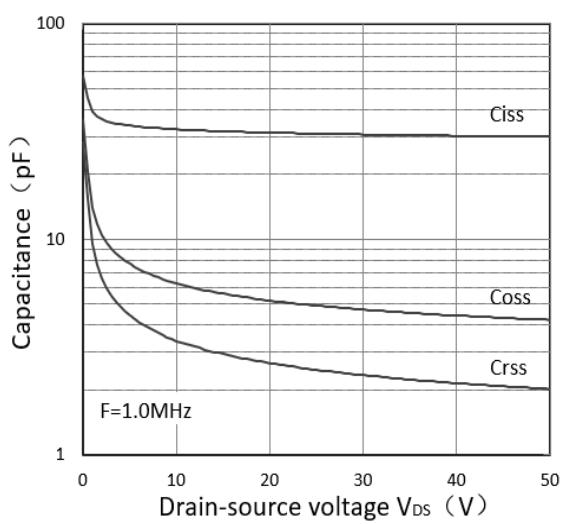
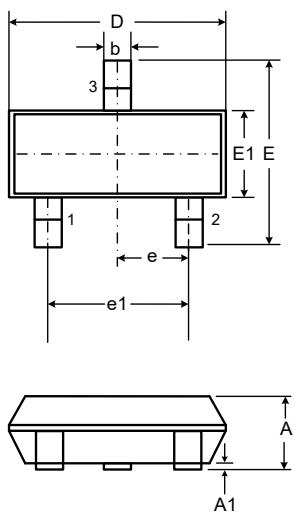
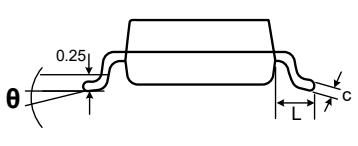
Figure 3. $R_{DS(ON)}$ vs. I_D Figure 5. I_S vs. V_{SD} Figure 4. $R_{DS(ON)}$ vs. V_{GS} 

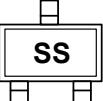
Figure 6. Capacitance Characteristics



Outline Drawing – SOT-23

PACKAGE OUTLINE			
			
			
DIMENSIONS		INCHES	
SYMBOL	MILLIMETER	MIN	MAX
A	0.90	1.15	0.035
A1	0.00	0.10	0.000
b	0.30	0.50	0.012
c	0.08	0.15	0.003
D	2.80	3.00	0.110
E	2.25	2.55	0.089
E1	1.20	1.40	0.047
e	0.95 BSC	0.0374 BSC	
e1	1.80	2.00	0.071
L	0.45	0.65	0.018
θ	0°	8°	0°
Notes			
1. Dimensioning and tolerances per ANSI Y14.5M, 1985. 2. Controlling Dimension: Inches 3. Pin 3 is the cathode (Unidirectional Only). 4. Dimensions are exclusive of mold flash and metal burrs.			

Marking Codes

Part Number	WM05N02M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
 The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
 Users should verify actual device performance in their specific applications.